



SI4435DYTR Information



For Reference Only

Part Number SI4435DYTR

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 30V 8A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI4435DYTR Specifications

Manufacturer Part Number SI4435DYTR Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series HEXFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 60nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2320pF @ 15V Vgs (Max) 240V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 20 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series HEXFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Ourrent - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Iv @ 250µA Gate Charge (Qg) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds 2320pF @ 15V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ 1d, Vgs Operating Temperature Supplier Device Package Package / Case	Manufacturer Part Number	SI4435DYTR
Package 8-SOIC (0.154", 3.90mm Width) Series HEXFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 60nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2320pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 20 mohm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	Infineon Technologies
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Series HEXFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 60nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2320pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 20 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 60nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2320pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 20 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs60nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2320pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs20 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	HEXFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs60nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2320pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs20 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 60nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 8A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs60nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2320pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs20 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs fonc @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	8A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2320pF @ 15V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs20 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	60nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	2320pF @ 15V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs20 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.5W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	20 mOhm @ 8A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

SI4435DYTR Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI4435DYTR Payment Methods





















SI4435DYTR Shipping Methods













If you have any question about SI4435DYTR, please do not hesitate to contact us!

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